

100V N-Channel MOSFETS

TO-252 Plastic-Encapsulate Transistors

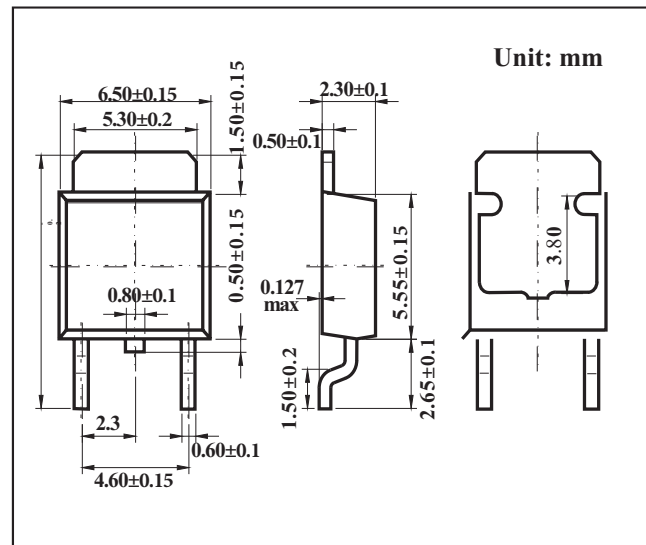
BVDSS	RDSON	ID
100V	115mΩ	12A

Features

- 100V,12A , $R_{DS(ON)}=115m\Omega@V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

Applications

- Networking
- Load Switch
- LED applications



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current – Continuous ($T_C=25^\circ C$)	I_D	12	A
Drain Current – Continuous ($T_C=100^\circ C$)		7.6	A
Drain Current – Pulsed ¹	I_{DM}	48	A
Single Pulse Avalanche Energy ²	EAS	6	mJ
Single Pulse Avalanche Current ²	IAS	11	A
Power Dissipation ($T_C=25^\circ C$)	P_D	34.7	W
Power Dissipation – Derate above 25°C		0.27	W/°C
Storage Temperature Range	T_{STG}	-50 to 150	°C
Operating Junction Temperature Range	T_J	-50 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance Junction to ambient	$R_{\theta JA}$	---	62	°C/W
Thermal Resistance Junction to Case	$R_{\theta JC}$	---	3.1	°C/W

Off Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
BV_{DSS} Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C, $I_D=1mA$	---	0.09	---	V/°C
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V, T_J=25^\circ C$	---	---	1	μA
		$V_{DS}=80V, V_{GS}=0V, T_J=125^\circ C$	---	---	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=10A$	---	95	115	mΩ
		$V_{GS}=4.5V, I_D=8A$	---	100	125	mΩ
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.6	2.2	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		---	-5	---	mV/°C
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_D=2A$	---	8.7	---	S

Dynamic and switching Characteristics

Total Gate Charge ^{3,4}	Q_g	$V_{DS}=50V, V_{GS}=10V, I_D=2A$	---	20	40	nC
Gate-Source Charge ^{3,4}	Q_{gs}		---	3.2	6	
Gate-Drain Charge ^{3,4}	Q_{gd}		---	3.6	7	
Turn-On Delay Time ^{3,4}	$T_{d(on)}$	$V_{DD}=50V, V_{GS}=10V, R_G=3.3\Omega$ $I_D=1A$	---	18	36	ns
Rise Time ^{3,4}	T_r		---	4	8	
Turn-Off Delay Time ^{3,4}	$T_{d(off)}$		---	40	80	
Fall Time ^{3,4}	T_f		---	3	6	
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, F=1MHz$	---	1400	2800	pF
Output Capacitance	C_{oss}		---	60	120	
Reverse Transfer Capacitance	C_{rss}		---	35	70	
Gate resistance	R_g	$V_{GS}=0V, V_{DS}=0V, F=1MHz$	---	2	4	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current	I_S	$V_G=V_D=0V$, Force Current	---	---	12	A
Pulsed Source Current	I_{SM}		---	---	24	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1	V
Reverse Recovery Time ³	t_{rr}	$I_S=1A, dI/dt=100A/\mu s, T_J=25^\circ C$	---	38	---	ns
Reverse Recovery Charge ³	Q_{rr}		---	27	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=11A, R_G=25\Omega$, Starting $T_J=25^\circ C$.
3. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

RATINGS AND CHARACTERISTIC CURVES

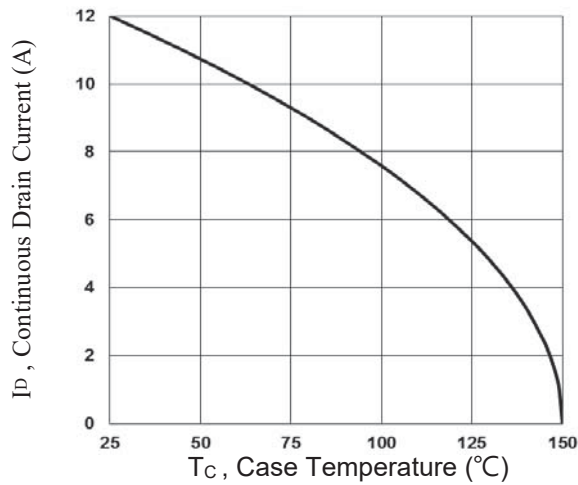


Fig.1 Continuous Drain Current vs. T_C

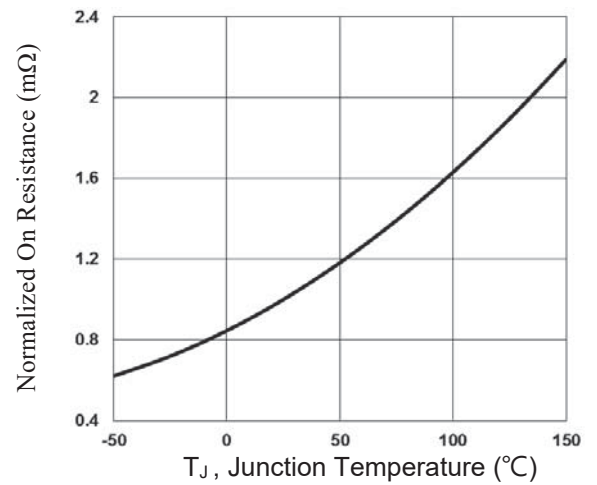


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

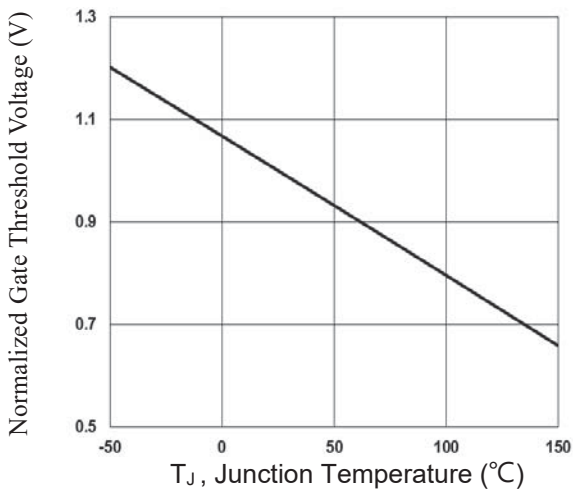


Fig.3 Normalized V_{th} vs. T_J

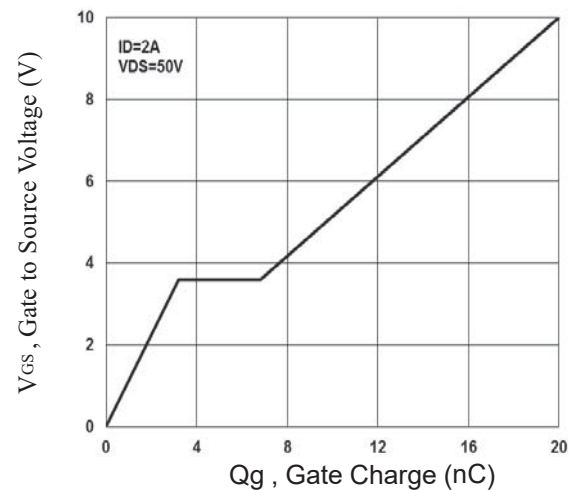


Fig.4 Gate Charge Waveform

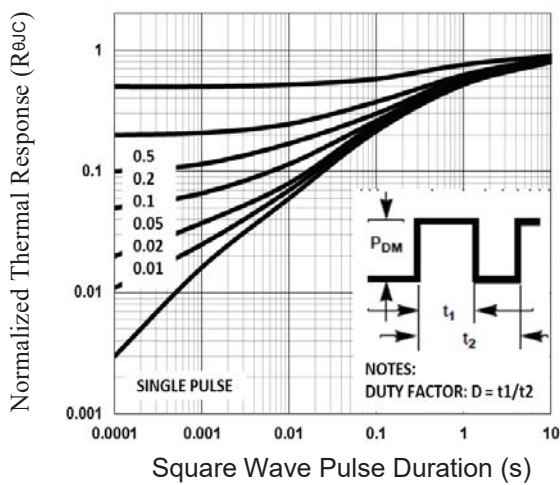


Fig.5 Normalized Transient Impedance

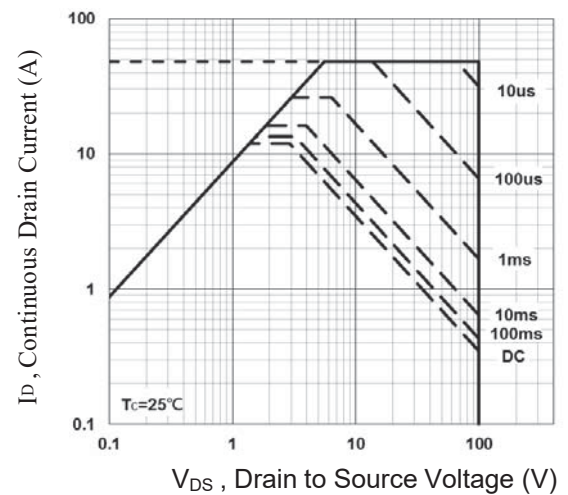


Fig.6 Maximum Safe Operation Area

RATINGS AND CHARACTERISTIC CURVES

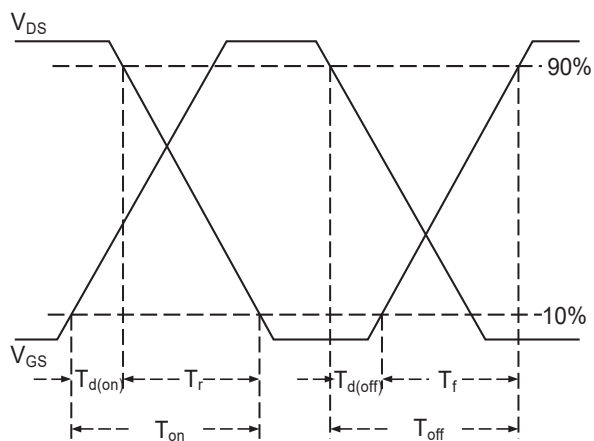


Fig.7 Switching Time Waveform

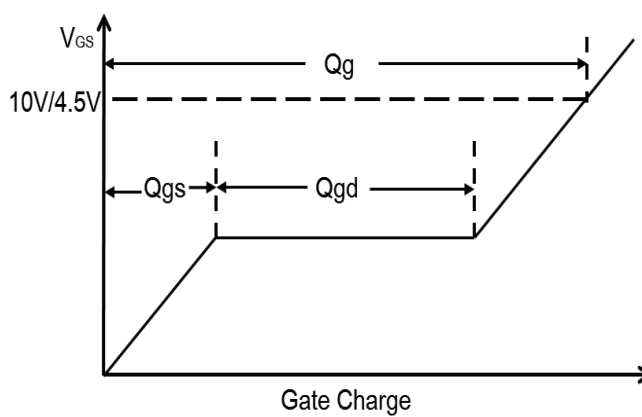


Fig.8 Gate Charge Waveform